

# **Device Modeling Report**

**COMPONENTS:**

DIODE/ GENERAL PURPOSE RECTIFIER/ STANDARD

PART NUMBER: 5GLZ47A

MANUFACTURER: TOSHIBA

REMARK: TC=110C

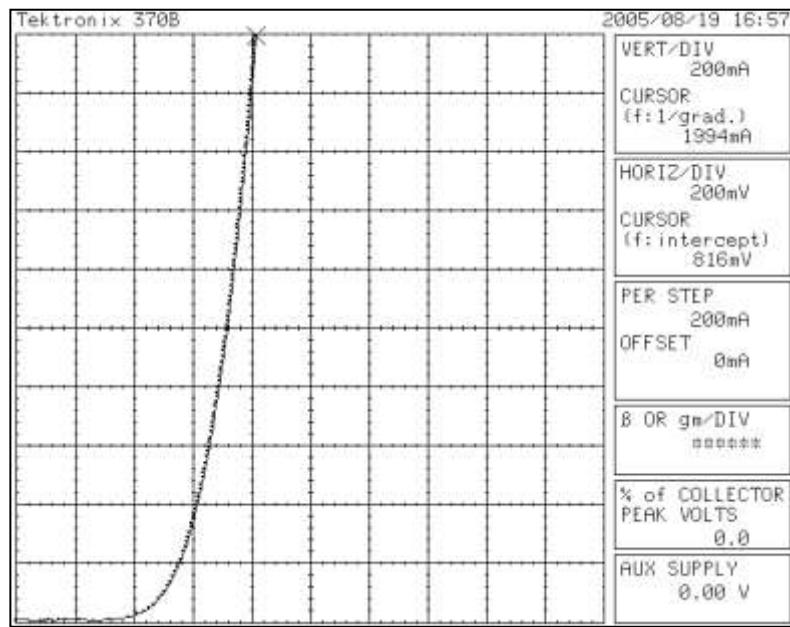


**Bee Technologies Inc.**

PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

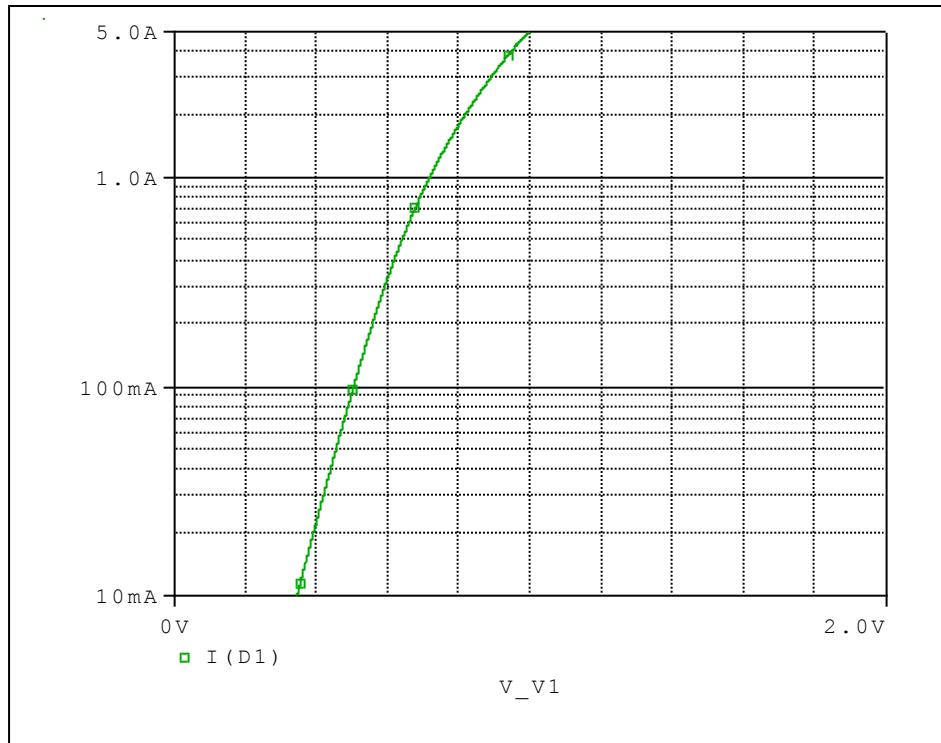
## Forward Current Characteristic

## Reference

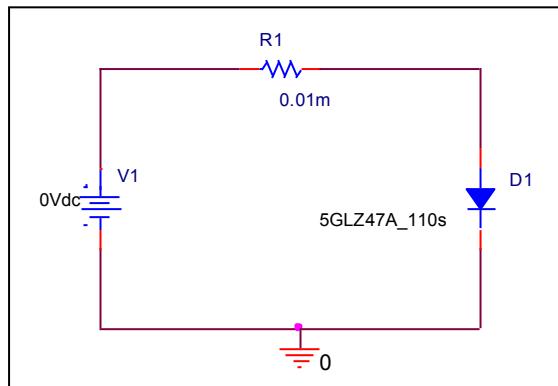


## Forward Current Characteristic

Circuit Simulation Result

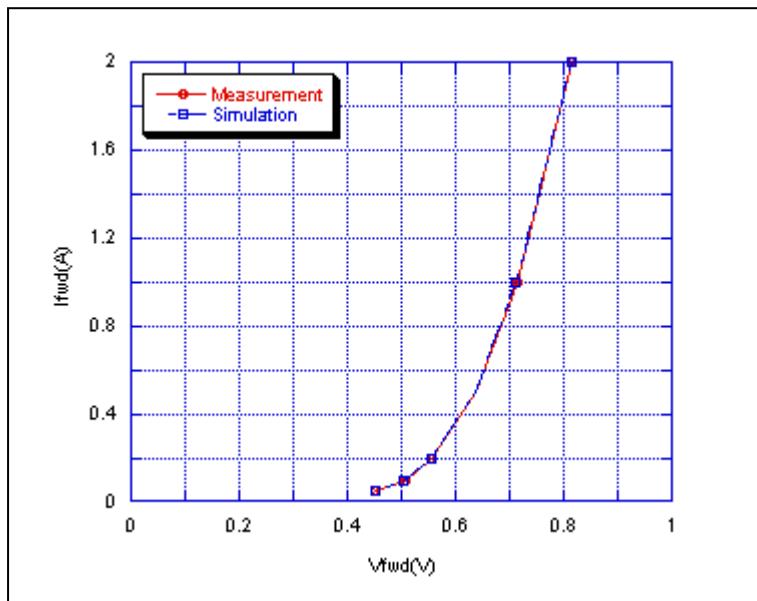


Evaluation Circuit



## Comparison Graph

### Circuit Simulation Result

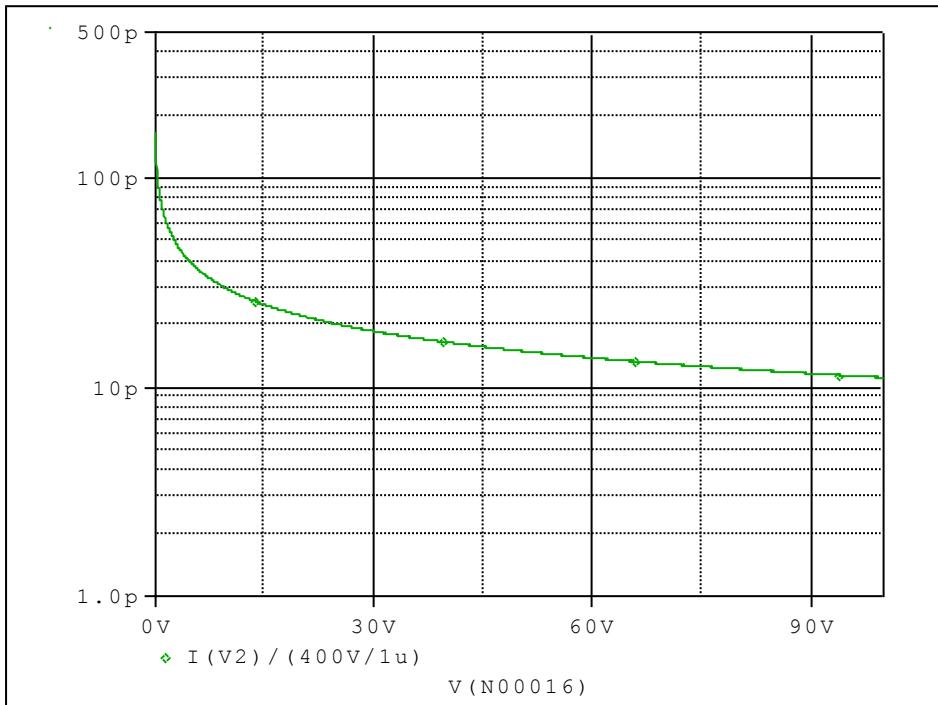


### Simulation Result

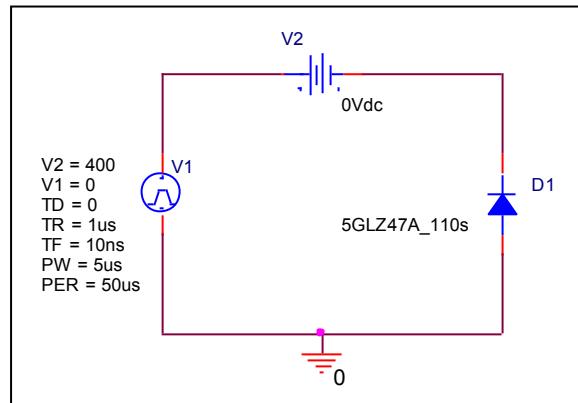
$I_{fwd}$ (A)	$V_{fwd}$ (V) Measurement	$V_{fwd}$ (V) Simulation	%Error
0.05	0.452	0.451	0.221
0.1	0.506	0.503	0.593
0.2	0.554	0.556	-0.361
0.5	0.638	0.637	0.157
1	0.716	0.712	0.559
2	0.816	0.815	0.123

## Capacitance Characteristic

### Circuit Simulation Result

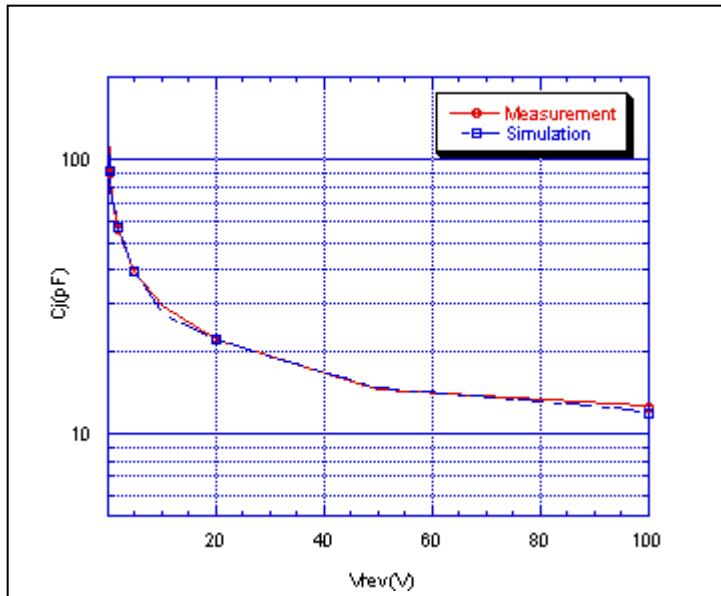


### Evaluation Circuit



## Comparison Graph

### Circuit Simulation Result

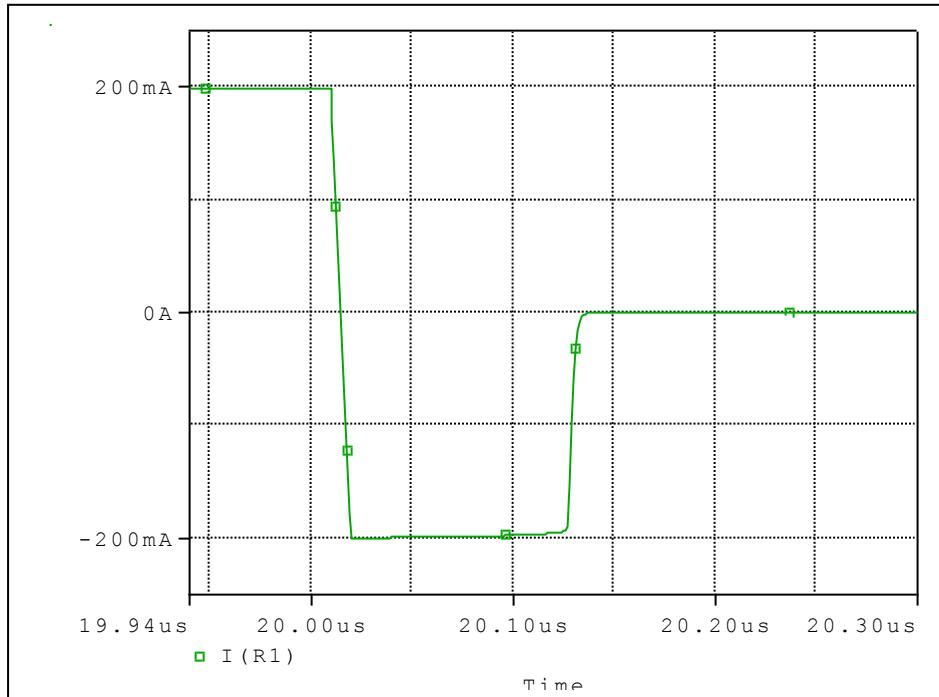


### Simulation Result

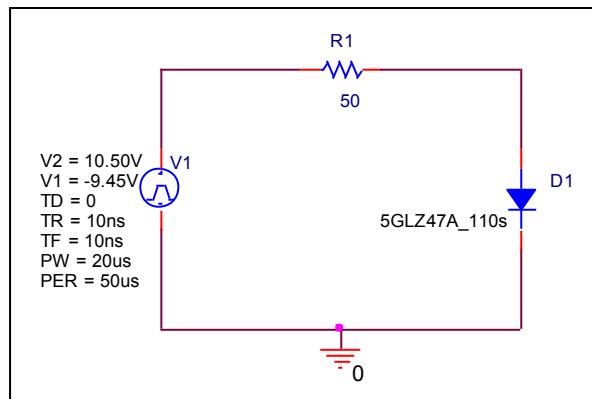
$V_{rev}$ (V)	$C_j$ (pF) Measurement	$C_j$ (pF) Simulation	%Error
0	143.500	143.500	0.000
0.5	89.800	90.200	-0.445
1	72.100	72.600	-0.693
2	55.600	56.400	-1.439
5	38.900	39.000	-0.257
10	29.300	29.000	1.024
20	22.000	22.000	0.000
50	14.600	14.900	-2.055
100	12.500	11.900	4.800

## Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit

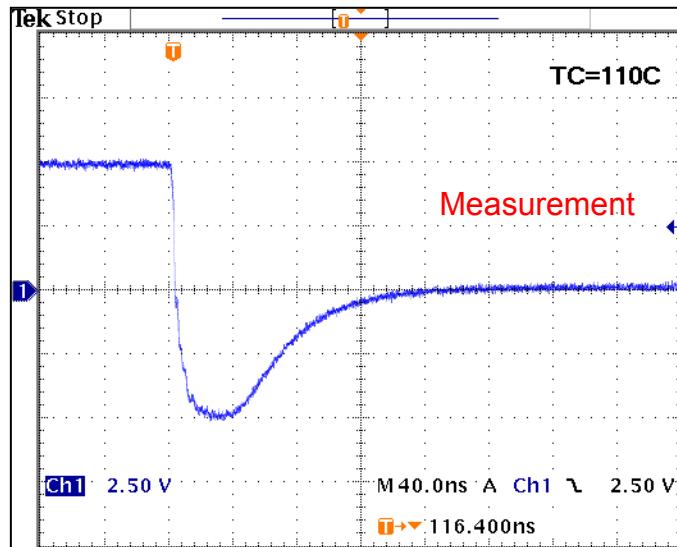


Compare Measurement vs. Simulation

	Measurement		Simulation		%Error
trr	116.00	ns	115.73	ns	0.233

## Reverse Recovery Characteristic

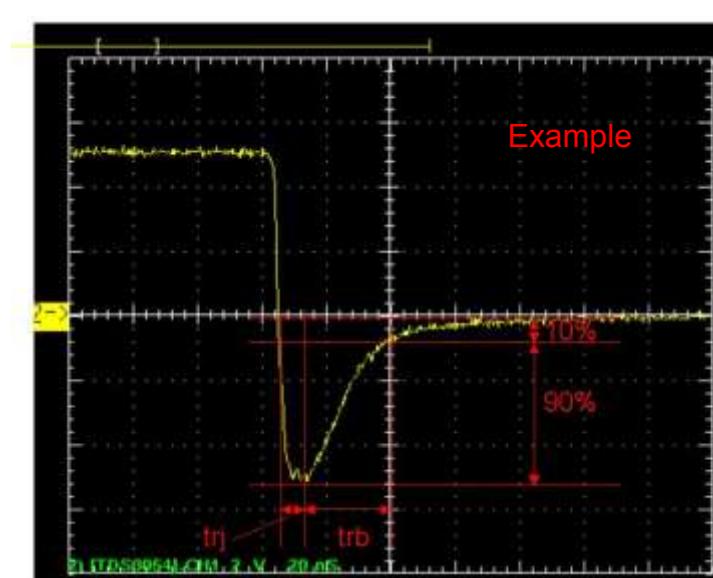
Reference



$Trj = 36 \text{ (ns)}$

$Trb = 80 \text{ (ns)}$

Conditions:  $I_{fwd}=I_{rev}=0.2(A)$ ,  $Rl=50$



Relation between  $trj$  and  $trb$